



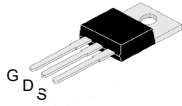
Continental Device India Pvt. Limited

An IATF 16949, ISO9001 and ISO 14001/ISO 45001 Certified Company

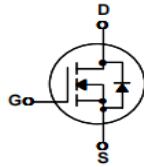


800V N-CHANNEL MOSFET

CD7N80



TO-220



**TO-220 Leaded
Plastic Package
RoHS compliant**

FEATURES:

1. Fast Switching
2. 100% avalanche tested
3. Improved dv/dt capability

APPLICATION:

1. Switch mode power supply (SMPS)
2. Uninterruptible power supply (UPS)
3. Power factor correction (PFC)

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C Unless otherwise specified)

PARAMETERS	SYMBOL	VALUE	UNIT
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	800	V
Continuous Drain Current	I_D	7	A
Pulse Drain Current ¹	I_{DM}	24	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulse Avalanche Energy ²	E_{AS}	180	mJ
Avalanche Current ¹	I_{AS}	7	A
Repetitive Avalanche Energy ¹	E_{AR}	0.72	mJ
Power Dissipation ($T_C = 25^\circ C$)	P_D	45.8	W
Operating Junction & storage Temperature Range	T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE

Thermal Resistance, Junction-to-Case	R_{thJC}	2.73	°C/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

CD7N80

Rev0_19072023EAW



Continental Device India Pvt. Limited

An IATF 16949, ISO9001 and ISO 14001/ISO 45001 Certified Company



ELECTRICAL CHARACTERISTICS at ($T_a = 25\text{ }^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
-----------	--------	-----------------	-----	-----	-----	------

STATIC CHARACTERISTICS

Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	800	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=800V, V_{GS}=0V, T_J=25^\circ C$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3.0	--	4.0	V
Drain-Source on-Resistance ³	$R_{DS(on)}$	$V_{GS}=10V, I_D=3A$	--	1.65	2.1	Ω

DYNAMIC CHARACTERISTICS

Input Capacitance	C_{iss}	$V_{GS}=10V,$ $V_{DS}=25V,$ $f=1.0MHz$	--	833	--	pF
Output Capacitance	C_{oss}		--	99	--	
Reverse Transfer Capacitance	C_{riss}		--	23	--	
Gate Resistance	R_g		--	2	--	
Total Gate Charge	Q_g	$V_{DD}=640V, I_D=6A,$ $V_{GS}=10A$	--	38	--	nC
Gate-Source Charge	Q_{gs}		--	4	--	
Gate-Drain Charge	Q_{gd}		--	24.5	--	
Turn-on delay Time	$t_{d(on)}$	$V_{DD}=400V, I_D=6A,$ $R_G=25\Omega$	--	37	--	nS
Turn-on Rise Time	t_r		--	16.5	--	
Turn-off delay Time	$t_{d(off)}$		--	100	--	
Turn-off Fall Time	t_f		--	32	--	

DRAIN-SOURCE BODY DIODE CHARACTERISTICS

Continuous Body Diode Current	I_S	$T_C = 25^\circ C$	--	--	7	A
Pulse Diode Forward Current	I_{SM}		--	--	24	
Body Diode Voltage	V_{SD}	$T_J=25^\circ C, I_{SD}=3A, V_{GS}=0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{DD}=400V, I_S=6A,$ $diF/dt=100A/\mu S$	--	510	--	ns
Reverse Recovery Charge	Q_{rr}		--	5.2	--	μC

Note:

1. Repetitive rating; pulse width limited by max. junction temperature
2. $L=10mH, V_{DD}=50V, R_G=25\Omega, \text{Starting } T_J = 25^\circ C$
3. Pulse Test: Pulse Width $\leq 300\ \mu s, \text{Duty Cycle } \leq 1\%$



Continental Device India Pvt. Limited

An IATF 16949, ISO9001 and ISO 14001/ISO 45001 Certified Company



TYPICAL CHARACTERISTICS CURVES

Fig. 1 : On - State Characteristics

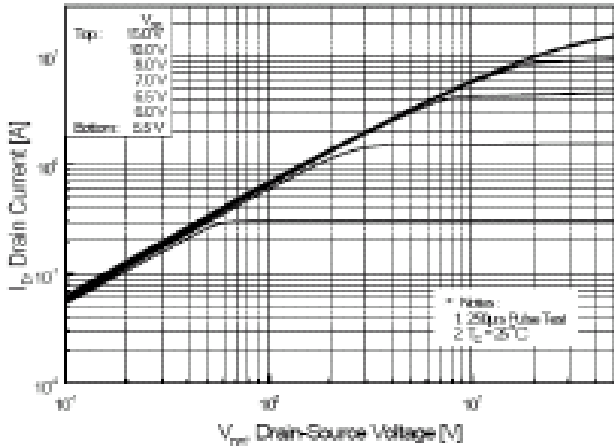


Fig. 2 : Transfer Characteristics

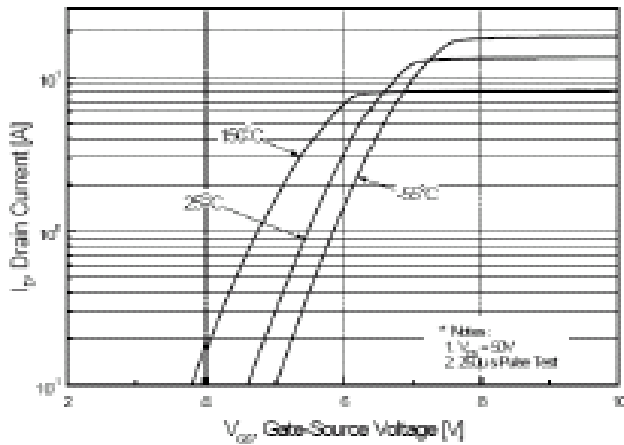


Fig. 3 : Breakdown Voltage Variation vs Temperature

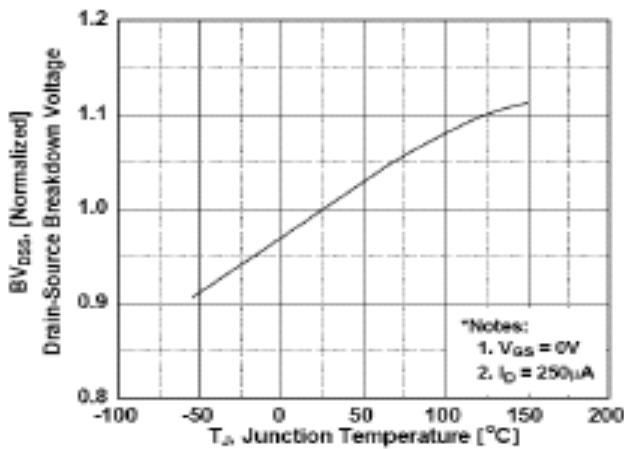


Fig. 4 : On - Resistance Variation vs Temperature

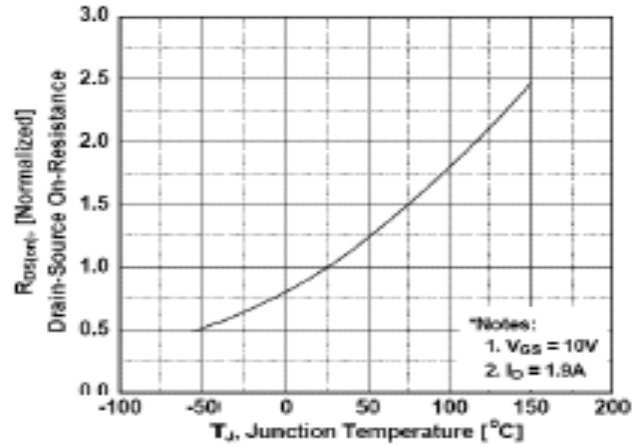


Fig. 5 : Capacitance Characteristics

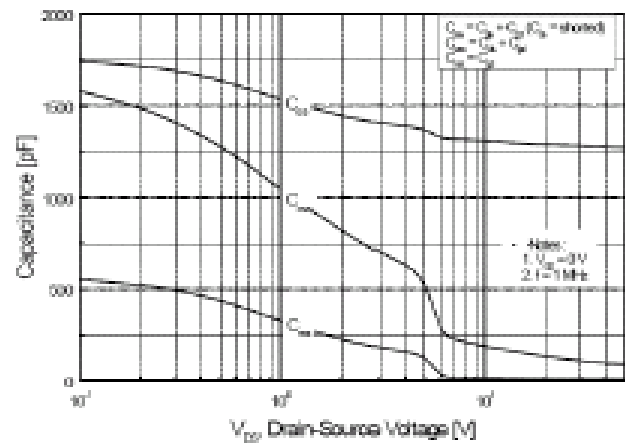
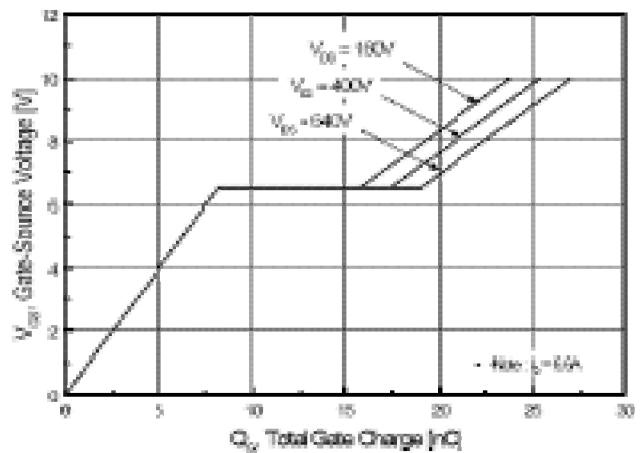


Fig. 5 : Capacitance Characteristics





Continental Device India Pvt. Limited

An IATF 16949, ISO9001 and ISO 14001/ISO 45001 Certified Company



TYPICAL CHARACTERISTICS CURVES

Fig. 7 : Maximum safe Operating Area

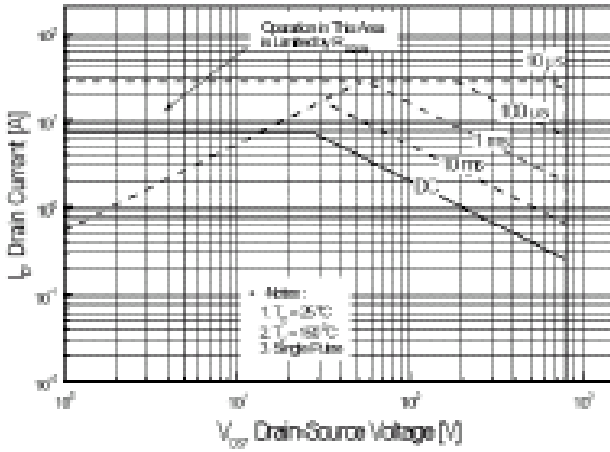


Fig. 8 : Maximum Drain Current vs Case Temperature

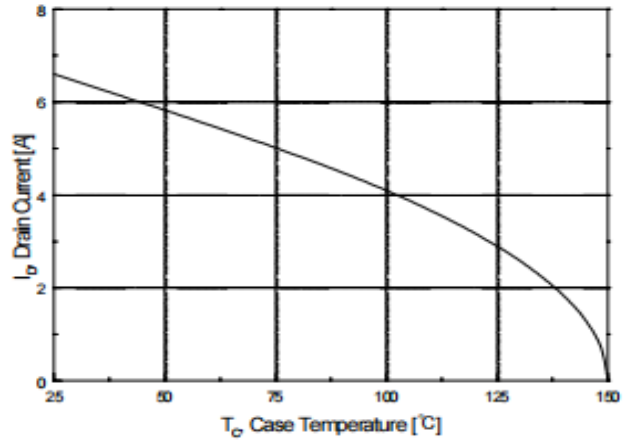
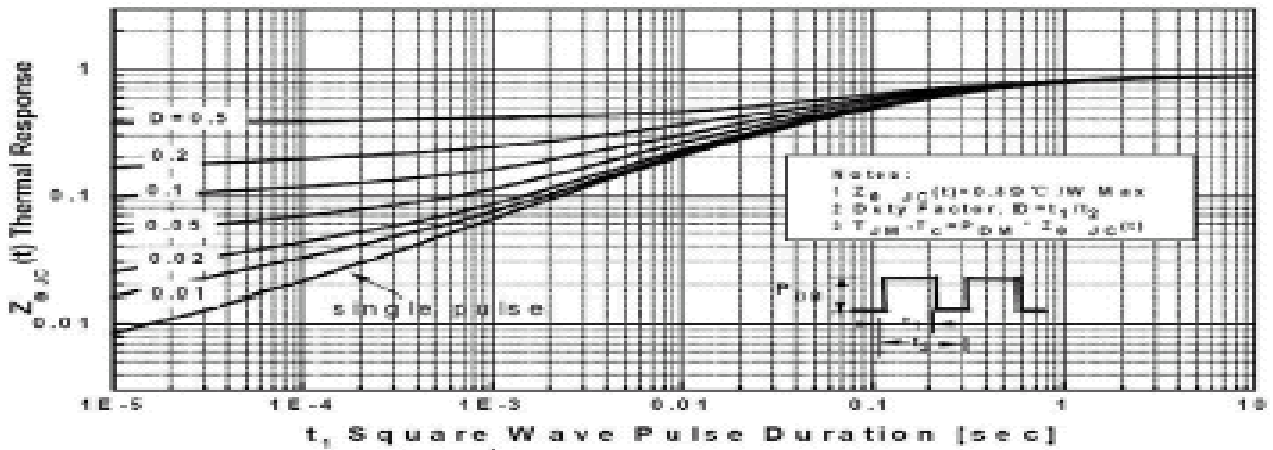


Fig. 9 : Transient Thermal Response Curve



Recommended Reflow Solder Profiles

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.

Figure 1

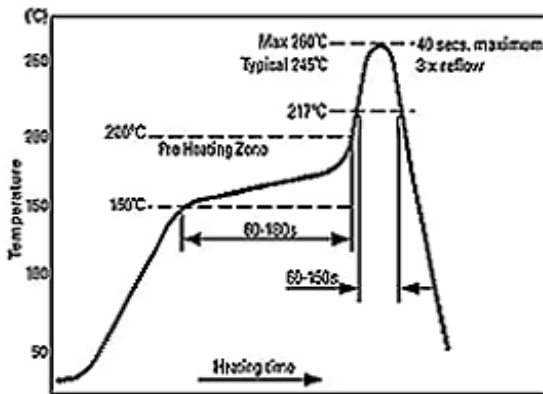
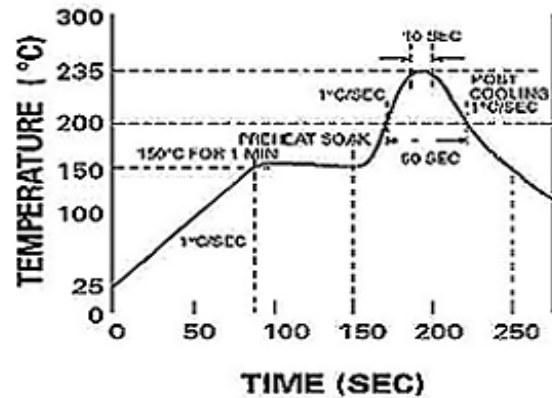


Figure 2

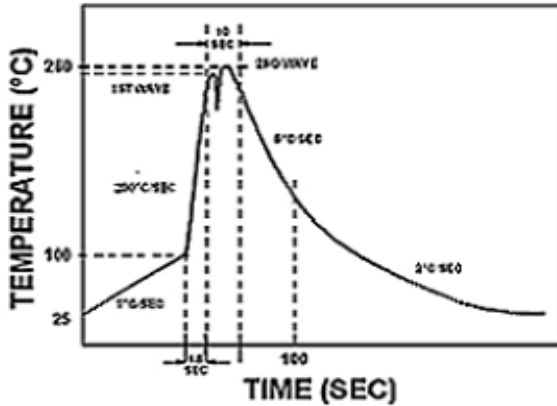


Reflow profiles in tabular form

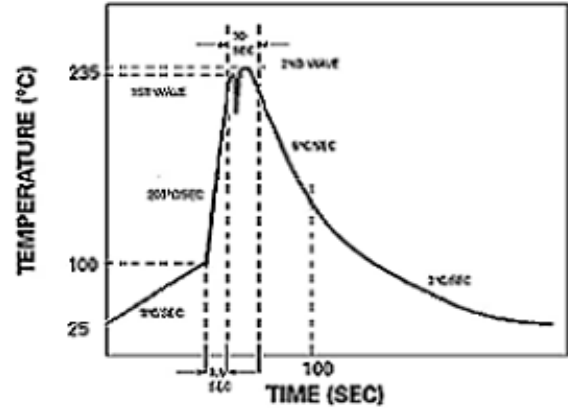
Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~3°C/second	~3°C/second
Preheat		
– Temperature Range	150-170°C	150-200°C
– Time	60-180 seconds	60-180 seconds
Time maintained above:		
– Temperature	200°C	217°C
– Time	30-50 seconds	60-150 seconds
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	40 seconds
Ramp-Down Rate	3°C/second max.	6°C/second max.

Recommended Wave Solder Profiles

The Recommended solder Profile For Devices with Pb-free terminal plating where a Pb-free solder is used



The Recommended solder Profile For Devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with leaded solder

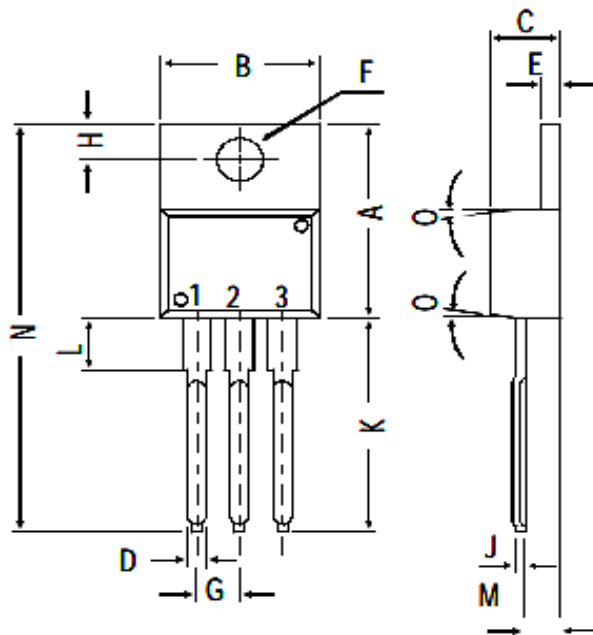


Wave Profiles in Tabular Form

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~200°C/second	~200°C/second
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	10 seconds
Ramp-Down Rate	5°C/second max.	5°C/second max

PACKAGE DETAILS

TO-220 Package Outline and Dimension

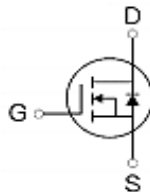


DIM	MIN	MAX
A	14.42	16.51
B	9.63	10.67
C	3.56	4.83
D		0.90
E	1.15	1.40
F	3.75	3.88
G	2.29	2.79
H	2.54	3.43
J		0.56
K	12.70	14.73
L	2.80	4.07
M	2.03	2.92
N		31.24
O	7°	

All Dimensions are in mm

Pin Configurations

1. Gate
2. Drain
3. Source





Continental Device India Pvt. Limited

An IATF 16949, ISO9001 and ISO 14001/ISO 45001 Certified Company



Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- Temperature 5 °C to 30 °C
- Humidity between 40 to 70 %RH
- Air should be clean.
- Avoid harmful gas or dust.
- Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- Avoid rapid change of temperature.
- Avoid condensation.
- Mechanical stress such as vibration and impact shall be avoided.
- The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level		
Level	Time	Condition
1	Unlimited	≤30 °C / 85% RH
2	1 Year	≤30 °C / 60% RH
2a	4 Weeks	≤30 °C / 60% RH
3	168 Hours	≤30 °C / 60% RH
4	72 Hours	≤30 °C / 60% RH
5	48 Hours	≤30 °C / 60% RH
5a	24 Hours	≤30 °C / 60% RH
6	Time on Label(TOL)	≤30 °C / 60% RH

CD7N80

Rev0_19072023EAW



Continental Device India Pvt. Limited

An IATF 16949, ISO9001 and ISO 14001/ISO 45001 Certified Company



Customer Notes

Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered trademark of

Continental Device India Pvt. Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.

Telephone +91-11-2579 6150, 4141 1112 Fax +91-11-2579 5290, 4141 1119

email@cdil.com www.cdil.com

CIN No. U32109DL1964PTC004291

CD7N80

Rev0_19072023EAW